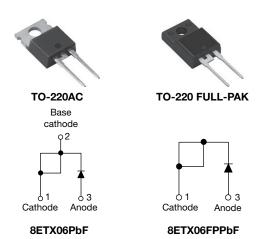




Vishay Semiconductors

Hyperfast Rectifier, 8 A FRED Pt®



PRODUCT SUMMARY				
Package	TO-220AC, TO-220FP			
I _{F(AV)}	8 A			
V_{R}	600 V			
V _F at I _F	3.0 V			
t _{rr} (typ.)	15 ns			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES

- Hyperfast recovery time
- · Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 approved
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level

DESCRIPTION/APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recover time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the ac-to-dc section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Repetitive peak reverse voltage	V_{RRM}		600	V	
Average restified forward current	I _{F(AV)}	T _C = 143 °C	8		
Average rectified forward current FULL-PAK		T _C = 106 °C	0	Α	
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	110	A	
Repetitive peak forward current	I _{FM}		18		
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-	.,	
Forward voltage	V _F	I _F = 8 A	-	2.3	3.0	V	
Forward voltage	v _F	I _F = 8 A, T _J = 150 °C	-	1.4	1.7		
Reverse leakage current	I_	$V_R = V_R$ rated	-	0.3	50		
Reverse leakage current I _R		$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	35	500	μΑ	
Junction capacitance	C _T	V _R = 600 V	=	17	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0 -		-	nΗ		

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply

VS-8ETX06PbF, VS-8ETX06FPPbF

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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
D		$I_F = 1 \text{ A}$, $dI_F/dt = 100 \text{ A/}\mu\text{s}$, $V_R = 30 \text{ V}$		-	15	19	
		I _F = 8 A, dI _F /dt = 100	A/ μ s, V _R = 30 V	-	16	24	ne
Reverse recovery time	t _{rr}	T _J = 25 °C	I _F = 8 A dI _F /dt = 200 A/μs V _R = 390 V	-	17	-	ns
		T _J = 125 °C		-	40	-	
Dools was assemble assemble	recovery current I _{RRM}	T _J = 25 °C		-	2.3	-	Α
Peak recovery current		T _J = 125 °C		-	4.5	-	A
Poverse recovery charge	D	T _J = 25 °C		-	20	-	nC
Reverse recovery charge Q _{rr}	Q _{rr}	T _J = 125 °C		-	100	-	110
Reverse recovery time	t _{rr}	T _J = 125 °C	I _F = 8 A dI _F /dt = 600 A/μs V _R = 390 V	-	31	-	ns
Peak recovery current	I _{RRM}			-	12	-	Α
Reverse recovery charge	Q _{rr}			-	195	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER SYMBOL		TEST CONDTIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}	T _J , T _{Stg}		-	175	°C
Thermal resistance,	Thermal resistance,		-	1.4	2	
junction to case (FULL-PAK)	R _{thJC}		-	3.4	4.3	
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Maight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Madding daving		Case style TO-220AC	8ETX06			
Marking device		Case style TO-220 FULL-PAK	8ETX06FP			



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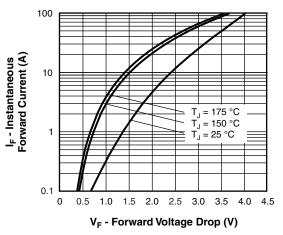


Fig. 1 - Typical Forward Voltage Drop Characteristics

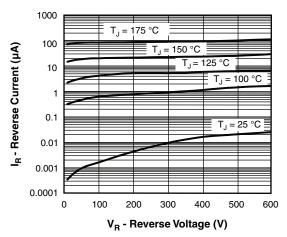


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

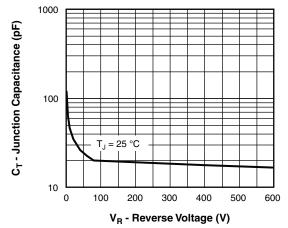


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

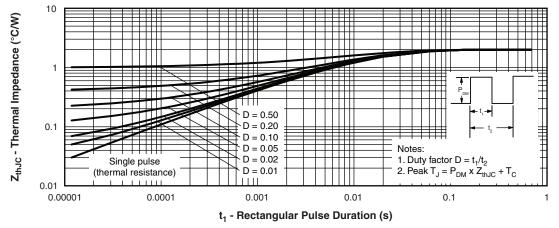


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

VS-8ETX06PbF, VS-8ETX06FPPbF

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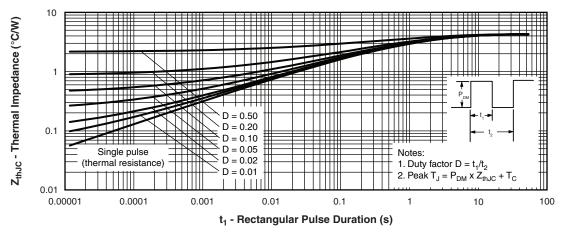


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)

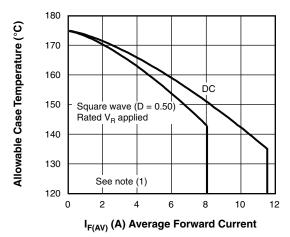
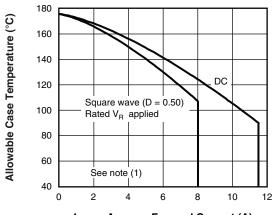
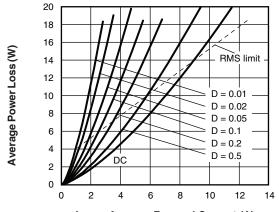


Fig. 6 - Maximum Allowable Case Temperature vs.
Average Forward Current



 $I_{F(AV)}$ - Average Forward Current (A)

Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)



I_{F(AV)} - Average Forward Current (A)

Fig. 8 - Forward Power Loss Characteristics

Note

 $\begin{array}{l} \text{(1)} \ \ \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8);} \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{Rated } V_R \\ \end{array}$



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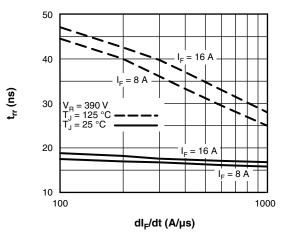


Fig. 9 - Typical Reverse Recovery Time vs. dI_F/dt

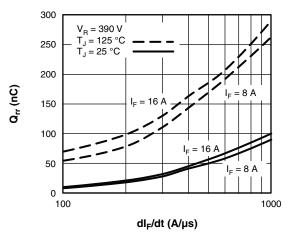


Fig. 10 - Typical Stored Charge vs. dl_F/dt

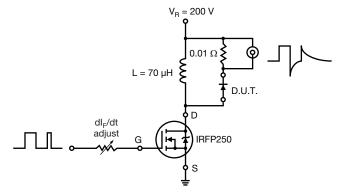
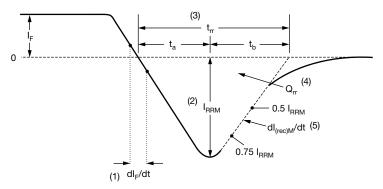


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RBM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_F$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 12 - Reverse Recovery Waveform and Definitions

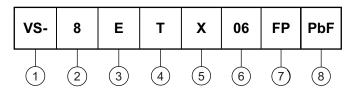
VS-8ETX06PbF, VS-8ETX06FPPbF

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ORDERING INFORMATION TABLE

Device code



HPP product suffix

2 - Current rating (8 = 8 A)

3 - E = Single diode

- T = TO-220, D²PAK

5 - X = Hyperfast rectifier

Voltage rating (06 = 600 V)

7 - • None = TO-220AC

• FP = TO-220 FULL-PAK

8 - • None = Standard production

• PbF = Lead (Pb)-free

Tube standard pack quantity: 50 pieces

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95039						
Part marking information	www.vishay.com/doc?95045					
SPICE model	www.vishay.com/doc?95393					

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